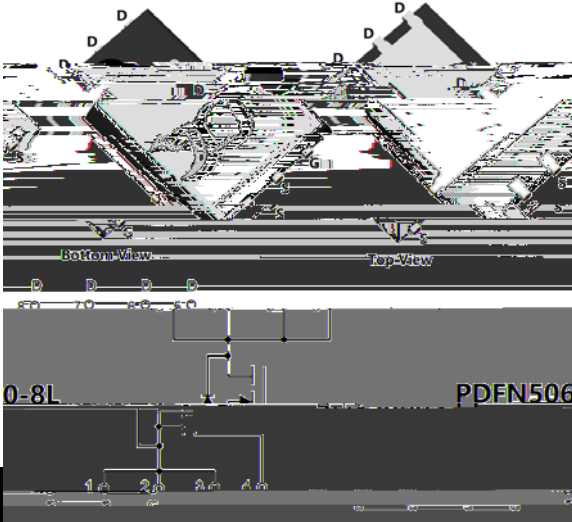


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

9_6
 $5_6 \ 2_1 \ D W \ 9 \ 9 \quad \emptyset \quad P R K P$
 $5_6 \ 2_1 \ D W \ 9 \ 9 \quad \emptyset \quad P R K P$
 $(\$ \ 7 H V W H G$
 $-9'6 \ 7 H V W H G$

General Description

" 6SOLW JDWH WUHQFK 026)(7 WHFKQROR
" ([FHOOHQW SDFNDW HGLR VLSDWLRQ
" +LJK GHQVLW\ FHOQ GHVLJQ IRU ORZ 5
" 3DUW QR ZLWKHQXVL\$(& 4 TXDOLILHG

FKLQJ
LFDWLRQ
PRđ€p€0 @pÀ X 0P@

*DWH VRXUFH 9ROWDJH		*6	9 “	9
UHQW	7F -	i		\$
	7F -			
3XOVHG 'UDLQ &XUUHQW		'0		\$
\$YDODQFKH ⁶ HQUHJ\		(\$6		P -

7 R W € „€Hö)%-Dy~i(8%-G™,2.òf,YrY H ò±BYt€ #™i(x,Yq H ó•-%-G™,2.ñ 'D& Æ € „€Hö %-G™,2.õ RYut„€ iv ,Yt€ #™iv ,Yt€ H û 4 % @0 0v

Parameter	Symbol	Typ	Max	Units
				- : 5
		287(5 & \$572		'(/,9(5< 02'(3 UH
	48\$17,7< S	48\$17,7< S		

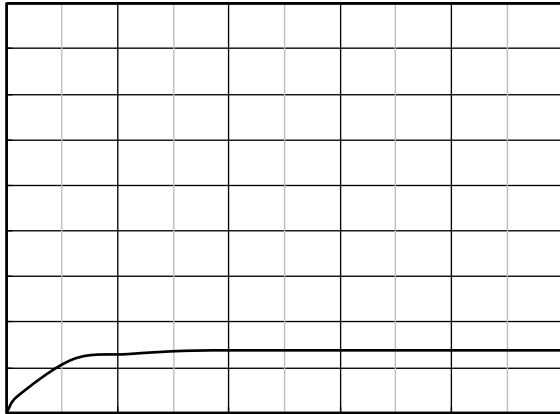


YJG95G06AQ

vElectrical Characteristics 7 XQOHVV RWKHUZZLVH QRWHG

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
'UDLQ 6RXUFH %UHDNGRZQ 9ROWDJH		*6 9%9, \$	9			9
=HUR *DWH 9ROWDJH 'UDLQ &XUHHQW		6 9,96 9	9			\$
*DWH %RG\ /HDNDJH &XUHHQW	*66	*6, " 9 9 9	9		"	Q\$
*DWH 7KUHVKROG 9ROWDJH	*6 WK	9 96 ', \$	9			9

Ω Typical Performance Characteristics



) L J X U H

2XWSXW &KDUDFWHULVWL FV

) L J X U H

7UDQV IHU &KD

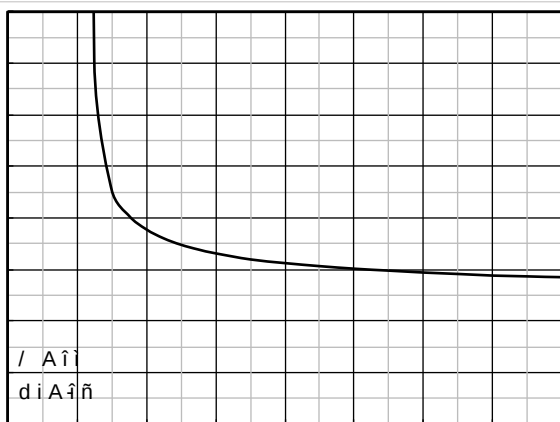
RDS(on) 'UDLQ WR 6RXUFH UHVLVWDQFH P

) L J X U H

& D S D F L F W D H Q U L H V W & K E W D

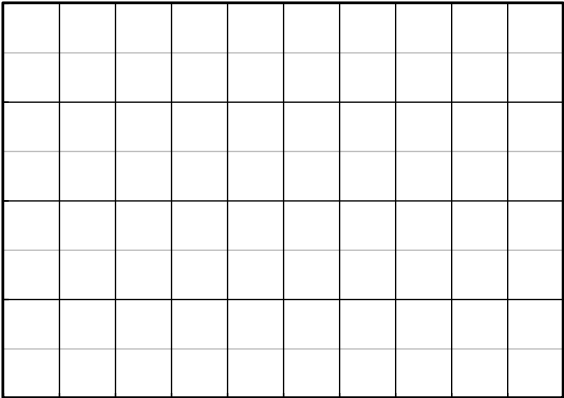
) L J X U H

* D W H & K



VGS *DWH WR 6RXUFH 9ROWDJH 9

)LJXUHQ 5HVLVWDQFH YV *DWH WR 6RXUFH) ~~1RUPDOLJHG~~ 2Q 5H

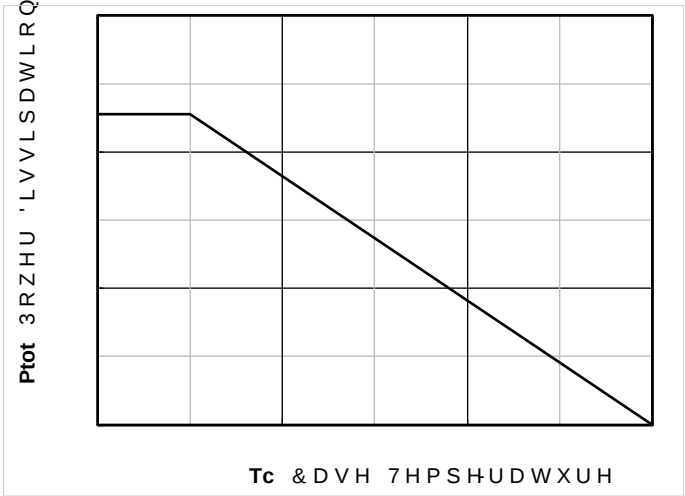


)LJXUH 6 RQ96 'UDLQ &XUUHQW

)R)UJZU6 FKDV DRA WHUWHUWHF G

)LJXUH 1RUPDOZQHGRDWDJNGR :

)LJXUH HG 71RU-PKORLQ G YRC



)LJXUH &XUUHQW GLVVLSDWLRQ

)LJXUH 3RZHU G

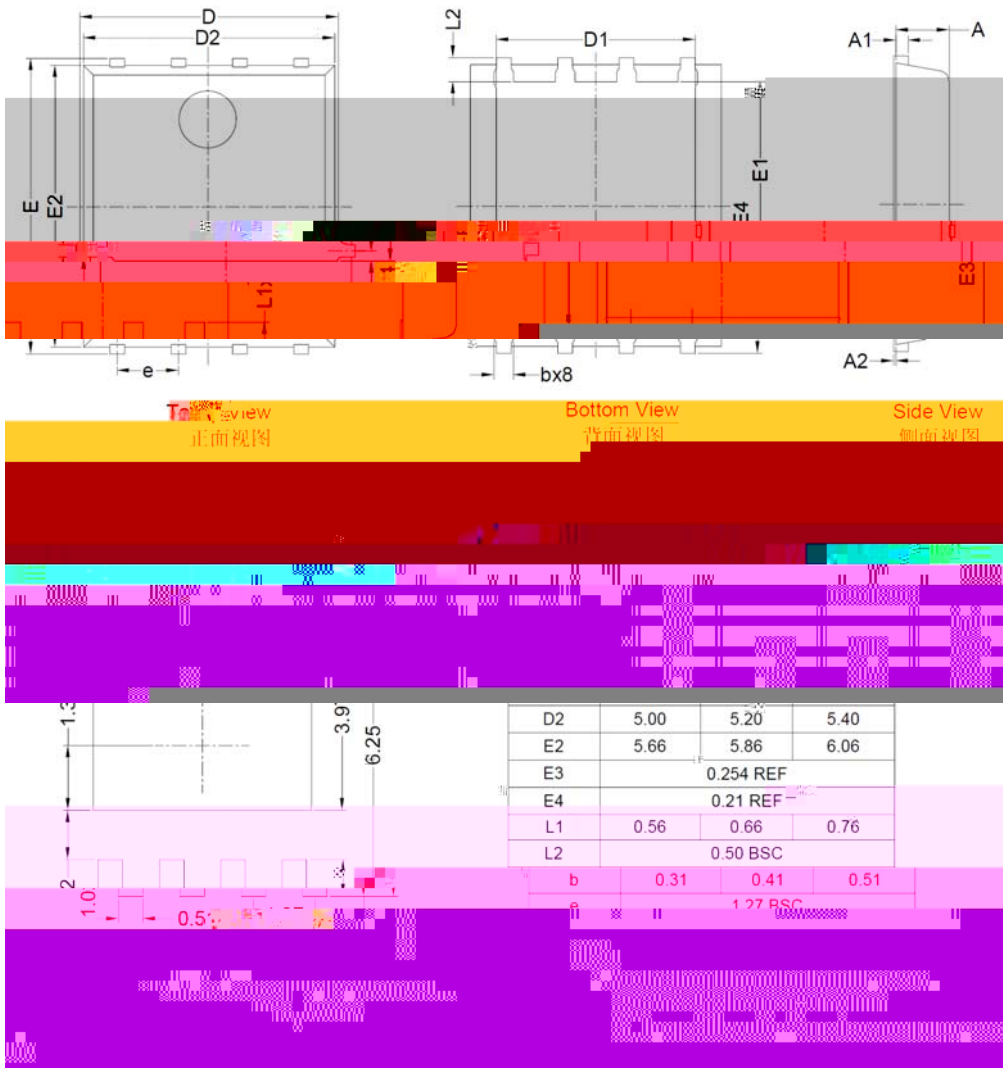


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YJG95G06AQ

vPDFN5060 Package information





7 KLV SXEOLFDFWLRQ SXDSFHUW DGDVLQURQAPDVLSFQLSGHYRLRDMGLRWQLSQDHDVQVRLPLWRX
KWWZSDQJMLHFRP